

PATENT APPLICATION
IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

DFW

Applicant: Nayfeh et al.
Serial No.: 10/829,486
Filed: April 22, 2004
Conf. No.: 6925
For: FAMILY OF DISCRETELY
SIZED SILICON
NANOPARTICLES AND
METHOD FOR PRODUCING
THE SAME
Art Unit: 1754
Examiner: Medina Sanabria, Maribel

I hereby certify that this paper is being deposited with the United States Postal Service as FIRST-CLASS mail in an envelope addressed to: Mail Stop AMENDMENT, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on this date.

April 8, 2005
Date

Attorney for Applicants
Registration No. 43,874

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Dear Sir:

This IDS is submitted under 37 C.F.R. §1.97(c), after the C.F.R. §1.97(b) time period, but before the mail date of a Final Office Action or a Notice of Allowance (whichever occurs first), with either:

- (a) a statement under 37 C.F.R. §1.97(e); or
- (b) the \$180.00 fee under 37 C.F.R. §1.17(p).

Applicant(s) submit herewith Form PTO-1449 (Information Disclosure Citation) together with copies of patents, publications or other information of which applicant(s) are aware, which applicant(s) believe may be material to the examination of this application and for which there may be a duty to disclose in accordance with 37 C.F.R. §1.56. Applicant(s) respectfully submit that the citation of any reference on Form PTO-1449 does not constitute an admission that the reference qualifies as prior art.

It is requested that the information disclosed on the enclosed Form PTO-1449 be made of record in this application.

(X) Statement Under 37 C.F.R. §1.97(e):

(X) The enclosed references were cited in a Communication issued by a foreign Patent Office (copy enclosed). Applicant(s) hereby certify that each item of information cited on the enclosed Form PTO-1449 was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three (3) months prior to the filing of this Information Disclosure Statement.

() Applicant(s) hereby certify that no item of information cited on the enclosed Form PTO-1449 was cited in a communication from a foreign patent office in a counterpart foreign application, and, to the knowledge of the person signing below after making reasonable inquiry, no item of information cited on the enclosed Form PTO-1449 was known to any individual designated in §1.56(c) more than three months prior to the filing of this Information Disclosure Statement.

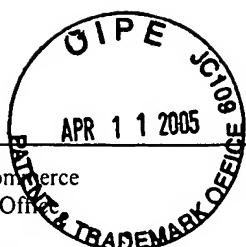
() Enclosed is a check for \$180.00 to cover the fee as set forth in 37 C.F.R. § 1.17(p).

The Commissioner is hereby authorized to charge any additional fees which may be required to this application under 37 C.F.R. §§1.16-1.17, or to credit any overpayment, to Deposit Account No. 07-2069. A duplicate copy of this sheet is enclosed.

Customer No. 24978
April 8, 2005
300 South Wacker Drive
Suite 2500
Chicago, Illinois 60606
Telephone: (312) 360-0080
Facsimile: (312) 360-9315
P:\DOCS\1201170367\903464.DOC

Respectfully submitted,
GREER, BURNS & CRAIN, LTD.

By:
Arik B. Ranson, Reg. No. 43,874

Form PTO-1449 U.S. Department of Commerce
(Rev. 8-88) Patent and Trademark Office

Attorney Docket No.: 1201.70367

Serial No.: 10/829,486

INFORMATION DISCLOSURE CITATION
(Use several sheets if necessary)

Applicant: Nayfeh et al.

Filing Date: April 22, 2004

Group: 1754

U.S. PATENT DOCUMENTS

Examiner Initial*	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate

FOREIGN PATENT DOCUMENTS

	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No
						Abs.	

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

	Fujii, M., Hayashi, S., Yamamoto, K., "Photoluminescence from B-Doped Si Nanocrystals," Journal of Applied Physics, American Institute of Physics, New York, Vol. 83, No. 12, June 15, 1998, pp. 7953-7957.
	Levoska, J., Tyunina, M., Leppävuori, S., "Laser Ablation Deposition of Silicon Nanostructures," NanoStructured Materials, Elsevier, New York, Published Online October 6, 1999, pp. 101-106.
	Brus, L., "Luminescence of Silicon Nanocrystals and Porous Silicon," Japanese Journal of Applied Physics, Publication Office Japanese Journal of Applied Physics, Tokyo, JP, Vol. 34, No. 34-1, Suppl., January 1994, pp. 5-7.

Examiner

Date Considered

*Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.